

# BUK98150-55A

N-channel TrenchMOS logic level FET

Rev. 04 — 11 June 2007

Product data sheet

## 1. Product profile

### 1.1 General description

N-channel enhancement mode power Field-Effect Transistor (FET) in a plastic package using NXP General Purpose Automotive (GPA) TrenchMOS technology.

### 1.2 Features

- Very low on-state resistance
- 150 °C rated
- Q101 compliant
- Logic level compatible

### 1.3 Applications

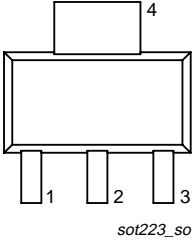
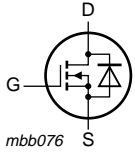
- Automotive systems
- Motors, lamps and solenoids
- General purpose power switching
- 12 V and 24 V loads

### 1.4 Quick reference data

- $E_{DS(AL)S} \leq 22$  mJ
- $I_D \leq 5.5$  A
- $R_{DS(on)} = 128$  m $\Omega$  (typ)
- $P_{tot} \leq 8$  W

## 2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	gate (G)	 <p style="text-align: center;"><small>sot223_so</small></p> <p style="text-align: center;"><b>SOT223 (SC-73)</b></p>	 <p style="text-align: center;"><small>mbb076</small></p>
2	drain (D)		
3	source (S)		
4	soldering point; connected to drain (D)		

### 3. Ordering information

**Table 2: Ordering information**

Type number	Package		Version
	Name	Description	
BUK98150-55A	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

### 4. Limiting values

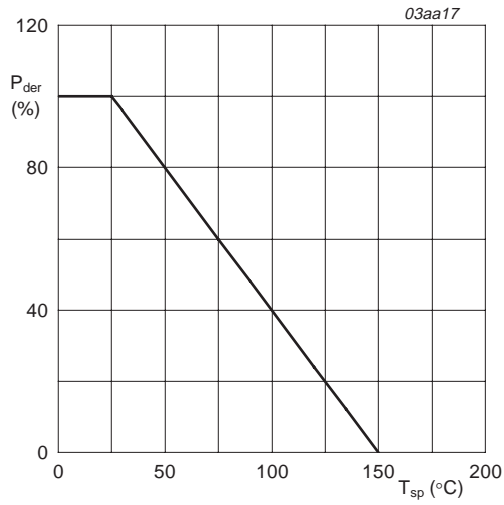
**Table 3. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	55	V
$V_{DGR}$	drain-gate voltage (DC)	$R_{GS} = 20 \text{ k}\Omega$	-	55	V
$V_{GS}$	gate-source voltage		-	$\pm 15$	V
$I_D$	drain current	$T_{sp} = 25 \text{ }^\circ\text{C}$ ; $V_{GS} = 5 \text{ V}$ ; see <a href="#">Figure 2</a> and <a href="#">3</a>	-	5.5	A
		$T_{sp} = 100 \text{ }^\circ\text{C}$ ; $V_{GS} = 5 \text{ V}$ ; see <a href="#">Figure 2</a>	-	3	A
$I_{DM}$	peak drain current	$T_{sp} = 25 \text{ }^\circ\text{C}$ ; pulsed; $t_p \leq 10 \text{ }\mu\text{s}$ ; see <a href="#">Figure 3</a>	-	22	A
$P_{tot}$	total power dissipation	$T_{sp} = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 1</a>	-	8	W
$T_{stg}$	storage temperature		-55	+150	$^\circ\text{C}$
$T_j$	junction temperature		-55	+150	$^\circ\text{C}$
<b>Source-drain diode</b>					
$I_{DR}$	reverse drain current	$T_{sp} = 25 \text{ }^\circ\text{C}$	-	5.5	A
$I_{DRM}$	peak reverse drain current	$T_{sp} = 25 \text{ }^\circ\text{C}$ ; pulsed; $t_p \leq 10 \text{ }\mu\text{s}$	-	22	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	unclamped inductive load; $I_D = 5.5 \text{ A}$ ; $V_{DS} \leq 55 \text{ V}$ ; $R_{GS} = 50 \text{ }\Omega$ ; $V_{GS} = 5 \text{ V}$ ; starting at $T_j = 25 \text{ }^\circ\text{C}$	-	22	mJ
$E_{DS(AL)R}$	repetitive drain-source avalanche energy		[1]	-	J

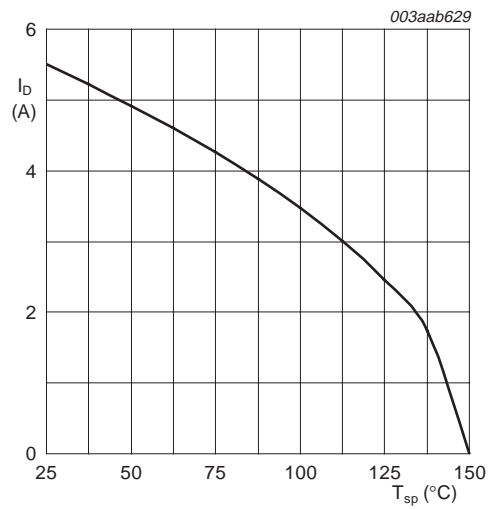
[1] Conditions:

- Value not quoted. Repetitive rating defined in [Figure 16](#).
- Single-pulse avalanche rating limited by  $T_{j(max)}$  of  $150 \text{ }^\circ\text{C}$ .
- Repetitive avalanche rating limited by an average junction temperature of  $145 \text{ }^\circ\text{C}$ .
- Refer to application note [AN10273](#) for further information.



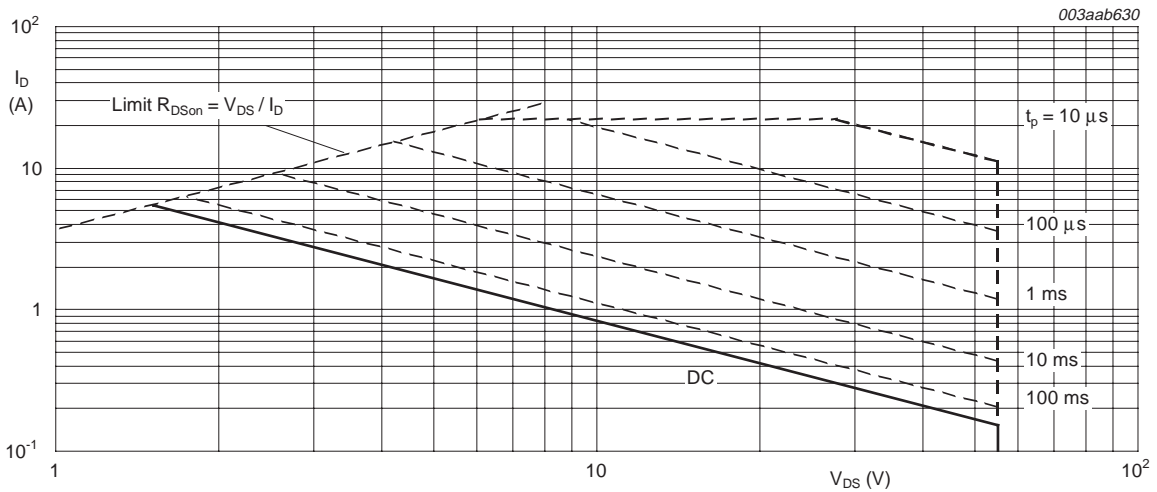
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

**Fig 1. Normalized total power dissipation as a function of solder point temperature**



V<sub>GS</sub> ≥ 5 V

**Fig 2. Continuous drain current as a function of solder point temperature**



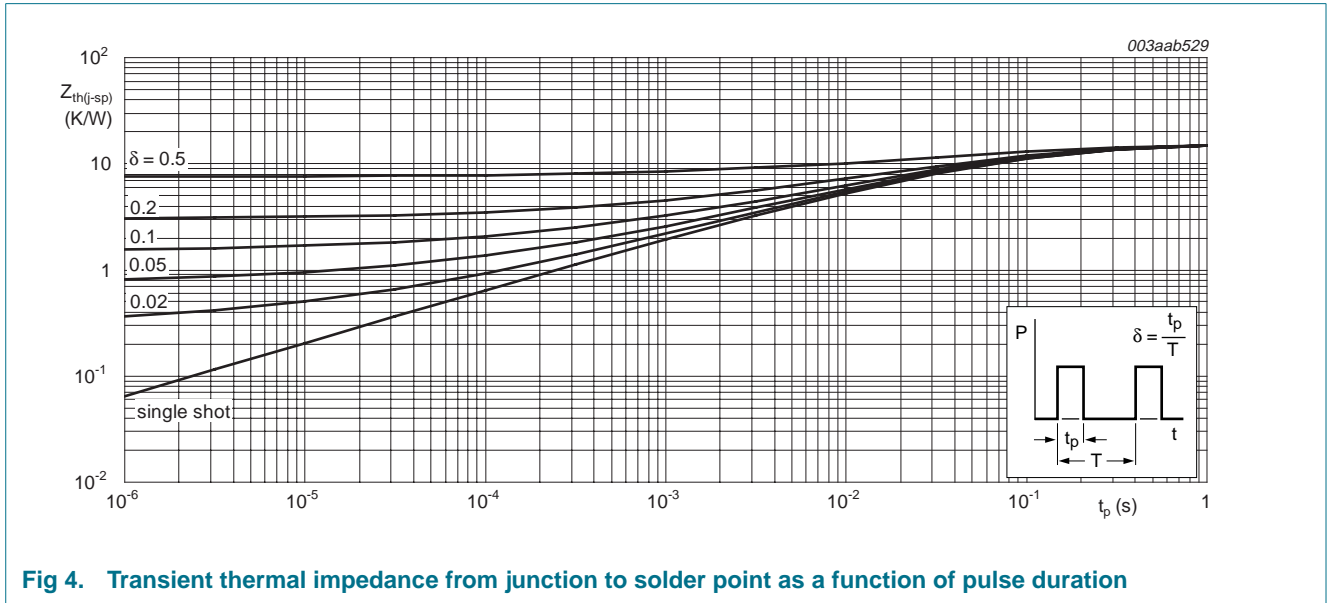
T<sub>sp</sub> = 25 °C; I<sub>DM</sub> is single pulse.

**Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

**5. Thermal characteristics**

**Table 4: Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	70	-	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	15	K/W

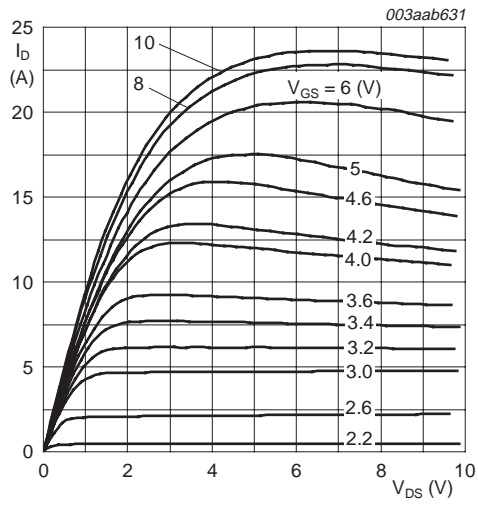


## 6. Characteristics

**Table 5: Characteristics**

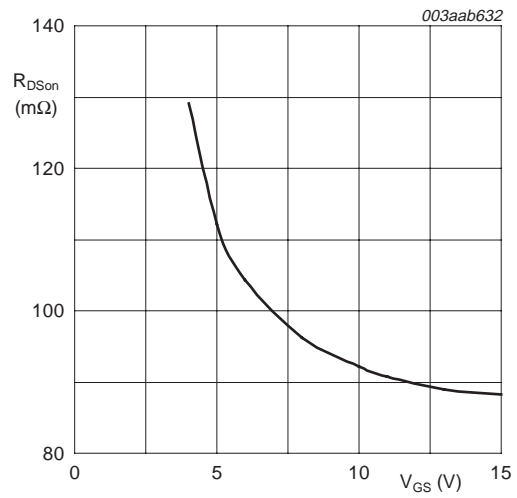
$T_j = 25\text{ °C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu\text{A}; V_{GS} = 0\ \text{V}$				
		$T_j = 25\text{ °C}$	55	-	-	V
		$T_j = -55\text{ °C}$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\ \text{mA}; V_{DS} = V_{GS}$ ; see <a href="#">Figure 9</a>				
		$T_j = 25\text{ °C}$	1	1.5	2	V
		$T_j = 150\text{ °C}$	0.6	-	-	V
		$T_j = -55\text{ °C}$	-	-	2.3	V
$I_{DSS}$	drain leakage current	$V_{DS} = 55\ \text{V}; V_{GS} = 0\ \text{V}$				
		$T_j = 25\text{ °C}$	-	0.05	10	$\mu\text{A}$
		$T_j = 150\text{ °C}$	-	-	500	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = \pm 15\ \text{V}; V_{DS} = 0\ \text{V}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 5\ \text{V}; I_D = 5\ \text{A}$ ; see <a href="#">Figure 7</a> and <a href="#">8</a>				
		$T_j = 25\text{ °C}$	-	128	150	m $\Omega$
		$T_j = 150\text{ °C}$	-	-	276	m $\Omega$
		$V_{GS} = 4.5\ \text{V}; I_D = 5\ \text{A}$	-	-	161	m $\Omega$
		$V_{GS} = 10\ \text{V}; I_D = 5\ \text{A}$	-	116	137	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 5\ \text{A}; V_{DD} = 44\ \text{V}; V_{GS} = 5\ \text{V}$ ; see <a href="#">Figure 14</a>	-	5.3	-	nC
$Q_{GS}$	gate-source charge		-	1	-	nC
$Q_{GD}$	gate-drain charge		-	2.8	-	nC
$C_{iss}$	input capacitance	$V_{GS} = 0\ \text{V}; V_{DS} = 25\ \text{V}; f = 1\ \text{MHz}$ ; see <a href="#">Figure 12</a>	-	240	320	pF
$C_{oss}$	output capacitance		-	53	64	pF
$C_{riss}$	reverse transfer capacitance		-	25	34	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 20\ \text{V}; R_L = 3.3\ \Omega$ ; $V_{GS} = 5\ \text{V}; R_G = 10\ \Omega$	-	8	-	ns
$t_r$	rise time		-	57	-	ns
$t_{d(off)}$	turn-off delay time		-	16	-	ns
$t_f$	fall time		-	13	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 5\ \text{A}; V_{GS} = 0\ \text{V}$ ; see <a href="#">Figure 15</a>	-	0.85	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 5\ \text{A}; dI_S/dt = -100\ \text{A}/\mu\text{s}$ ;	-	24	-	ns
$Q_r$	recovered charge	$V_{GS} = -10\ \text{V}; V_R = 30\ \text{V}$	-	30	-	nC



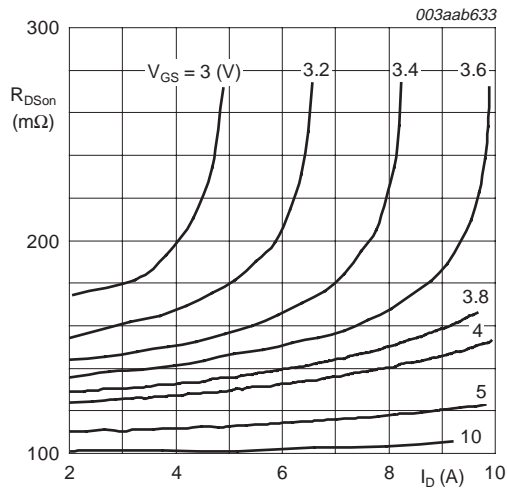
$T_j = 25\text{ }^\circ\text{C}$

**Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values**



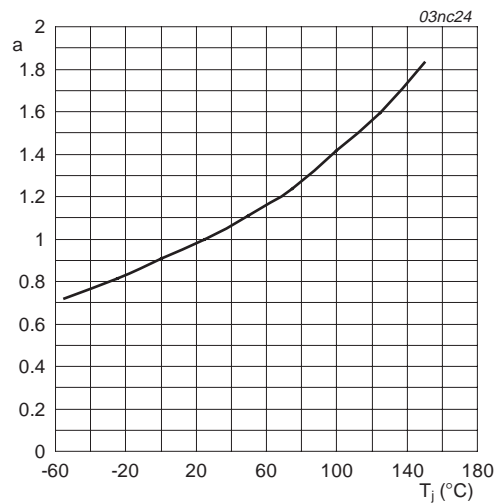
$T_j = 25\text{ }^\circ\text{C}; I_D = 5\text{ A}$

**Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values**



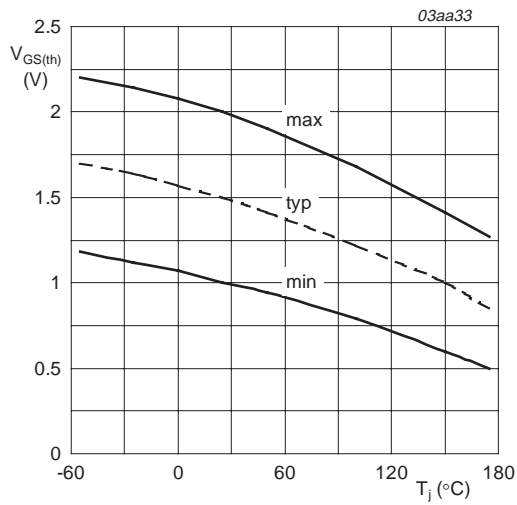
$T_j = 25\text{ }^\circ\text{C}$

**Fig 7. Drain-source on-state resistance as a function of drain current; typical values**



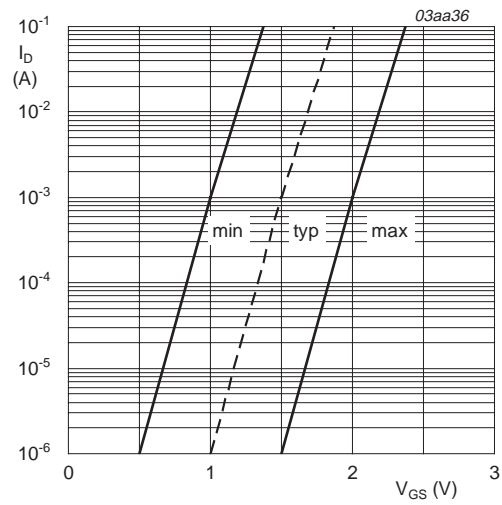
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

**Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature**



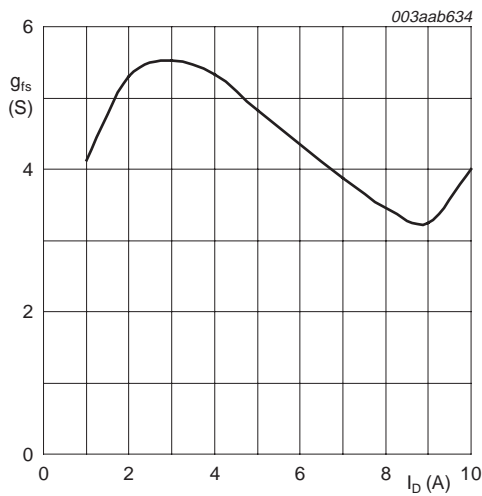
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

**Fig. 9. Gate-source threshold voltage as a function of junction temperature**



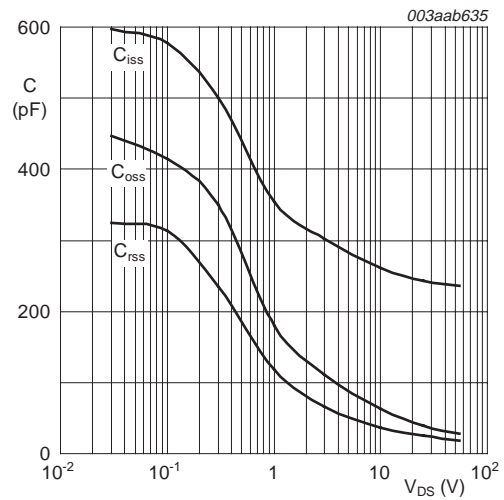
$T_j = 25 \text{ °C}; V_{DS} = V_{GS}$

**Fig. 10. Sub-threshold drain current as a function of gate-source voltage**



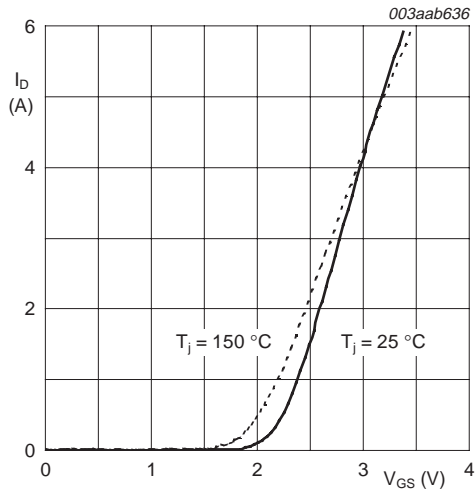
$T_j = 25 \text{ °C}; V_{DS} = 25 \text{ V}$

**Fig. 11. Forward transconductance as a function of drain current; typical values**



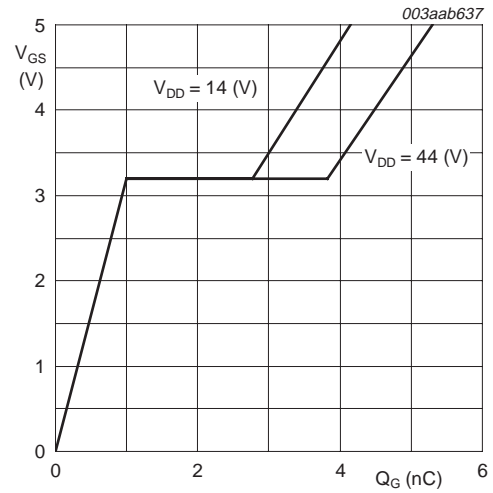
$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

**Fig. 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



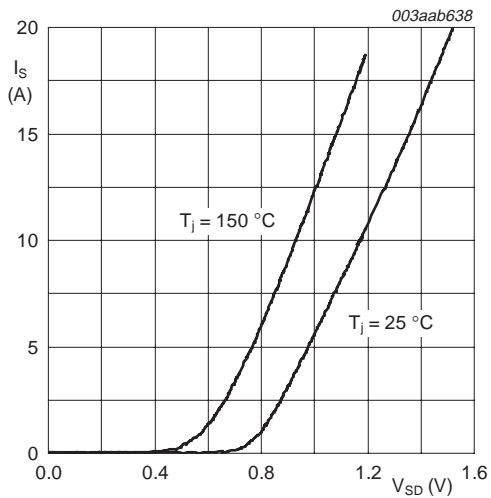
$V_{DS} = 25\text{ V}$

**Fig 13. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



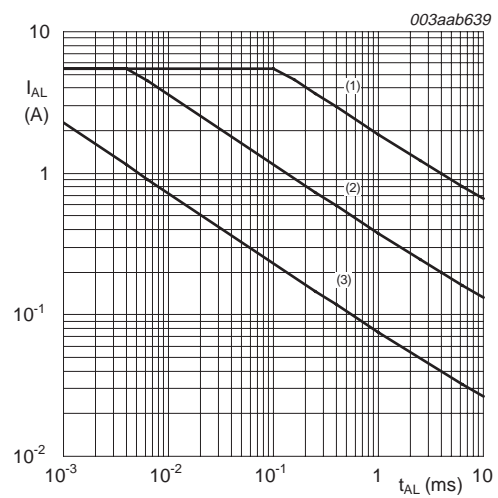
$T_j = 25\text{ }^\circ\text{C}; I_D = 5\text{ A}$

**Fig 14. Gate-source voltage as a function of gate charge; typical values**



$V_{GS} = 0\text{ V}$

**Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values**



See [Table note 1](#) of [Table 3](#) Limiting values.

- (1) Single-pulse;  $T_j = 25\text{ }^\circ\text{C}$ .
- (2) Single-pulse;  $T_j = 125\text{ }^\circ\text{C}$ .
- (3) Repetitive.

**Fig 16. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time**



**7. Package outline**

Plastic surface-mounted package with increased heatsink; 4 leads

SOT223

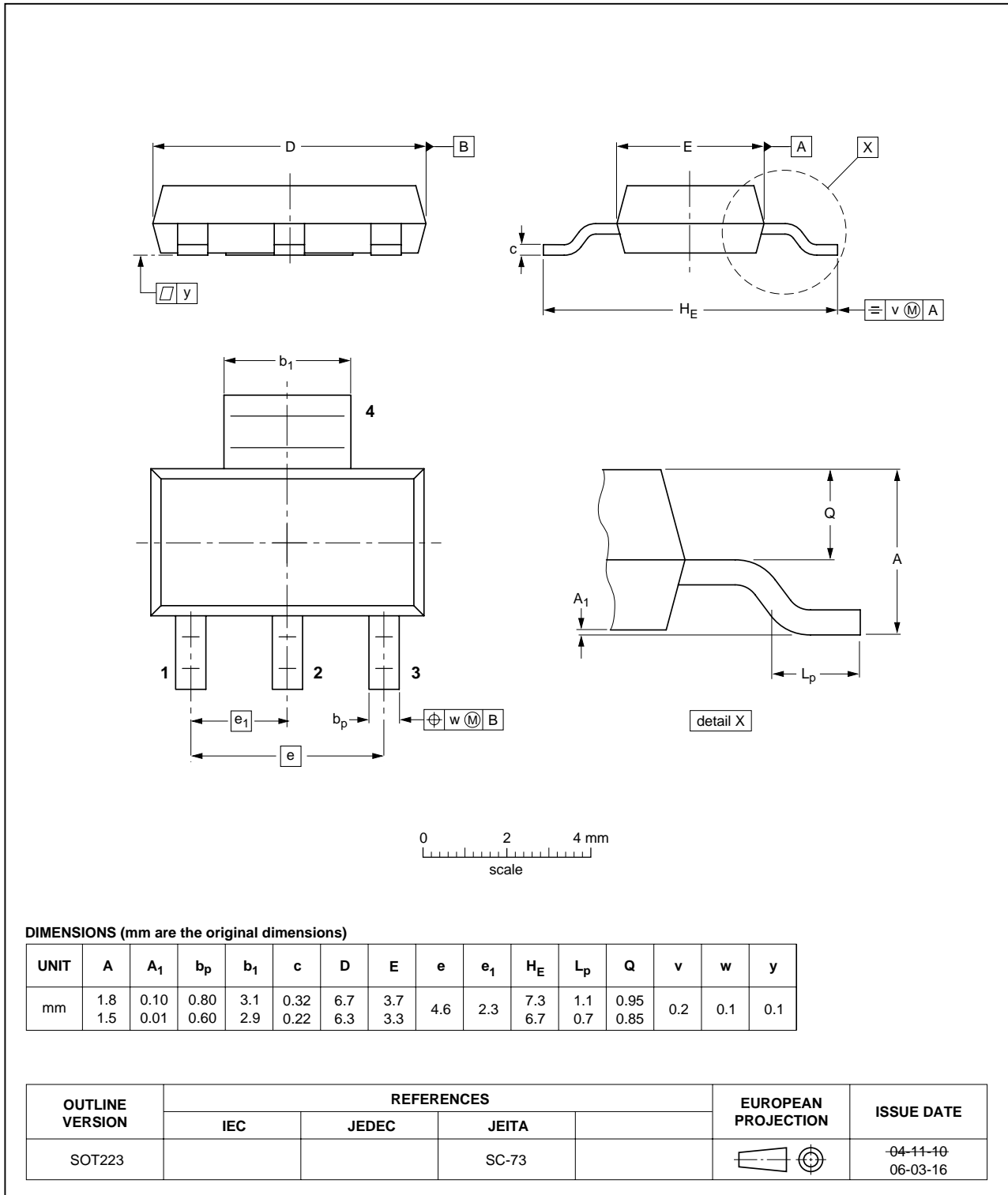
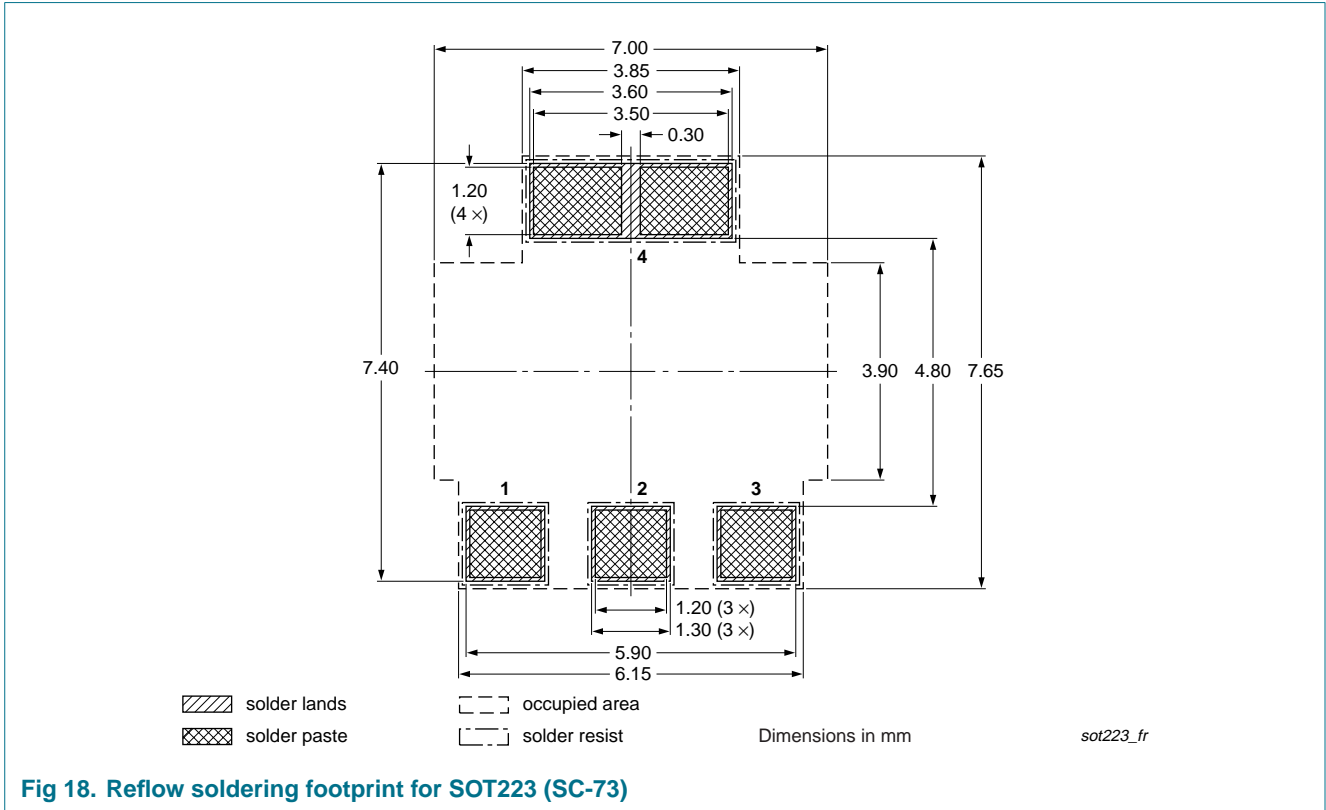


Fig 17. Package outline SOT223 (SC-73)

**8. Soldering**



**Fig 18. Reflow soldering footprint for SOT223 (SC-73)**

## 9. Revision history

**Table 6. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK98150-55A_4	20070611	Product data sheet	-	BUK98150-55A_3
Modifications:	<ul style="list-style-type: none"> <li>• <a href="#">Table 5</a>: IDSS drain leakage current condition changed from <math>T_j = 175\text{ °C}</math> to <math>T_j = 150\text{ °C}</math> due to typing error.</li> </ul>			
BUK98150-55A_3	20061124	Product data sheet	-	BUK98150-55A_2
Modifications:	<ul style="list-style-type: none"> <li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> <li>• Legal texts have been adapted to the new company name where appropriate.</li> <li>• Table 5: changed Typ and Max <math>C_{OSS}</math> output capacitance values from 40 pF to 53 pF and 48 pF to 64 pF respectively because of typing error.</li> </ul>			
BUK98150-55A_2	20020325	Product data sheet	-	BUK98150-55A_1
Modifications:	<ul style="list-style-type: none"> <li>• Table 3: Gate-source voltage maximum increased from <math>\pm 10\text{ V}</math> to <math>\pm 15\text{ V}</math></li> <li>• Table 4: <math>R_{th(j-sp)}</math> maximum decreased from 20 K/W to 15 K/W</li> <li>• Table 5: Switching speed measurements updated</li> <li>• Section 1.4 and Table 3: Total power dissipation, peak drain current, peak reverse drain current, and non-repetitive avalanche energy values updated.</li> </ul>			
BUK98150-55A_1	20001003	Product data sheet	-	-

## 10. Legal information

### 10.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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**12. Contents**

**1 Product profile . . . . . 1**

1.1 General description . . . . . 1

1.2 Features . . . . . 1

1.3 Applications . . . . . 1

1.4 Quick reference data . . . . . 1

**2 Pinning information . . . . . 1**

**3 Ordering information . . . . . 2**

**4 Limiting values . . . . . 2**

**5 Thermal characteristics . . . . . 4**

**6 Characteristics . . . . . 5**

**7 Package outline . . . . . 9**

**8 Soldering . . . . . 10**

**9 Revision history . . . . . 11**

**10 Legal information . . . . . 12**

10.1 Data sheet status . . . . . 12

10.2 Definitions . . . . . 12

10.3 Disclaimers . . . . . 12

10.4 Trademarks . . . . . 12

**11 Contact information . . . . . 12**

**12 Contents . . . . . 13**

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